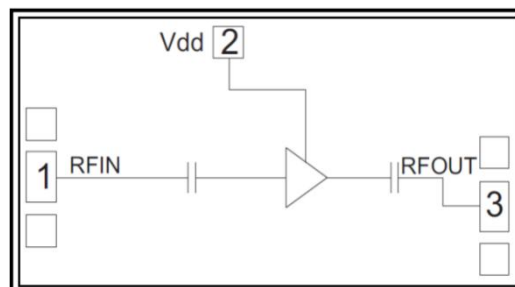


GaAs MMIC Low Noise Amplifier Chip, 0.5-20GHz

Performance characteristics

- Frequency range: 0.5-20GHz
- Small signal gain: 13dB
- Noise figure: 1.9dB typ.
- P-1dB: 13.5dBm
- Power supply: +5V/20mA(static state)
- Input/Output: 50Ohm
- 100% on-chip testing
- Chip size: 1.6 x 0.95 x 0.1 mm

Functional Block Diagram



Product Introduction

GLA-0020M is a broadband low-noise amplifier chip, with a frequency range of 0.5GHz~20GHz, a small signal gain of 13dB, an in band noise figure of 1.9dB, and a P-1 power of 13.5dBm. The GLA-0020M adopts a +5V single power supply, and the chip is compatible with a +3.5V power supply.

Use restriction parameters¹

Maximum leakage voltage	+7V
Maximum input power	+20dBm
Working temperature	-55 ~ +85°C
Storage temperature	-65 ~ +150°C

【1】 Exceeding any of the above maximum limits may result in permanent damage.

Electrical performance parameters($T_A = +25^\circ\text{C}$, $V_d = +5\text{V}$)

Index	Minimum value	Typical value	Maximum value	Unit
Frequency range	0.5-20			GHz
Small signal gain	-	13	-	dB
Gain flatness		± 0.5		dB
Noise figure	-	1.9	-	dB
P-1dB	-	13.5	-	dBm
Psat	-	17	-	dBm
Input return loss	-	15	-	dB
Output return Loss	-	15	-	dB
Static current	-	20	-	mA
P-1 current		30		mA

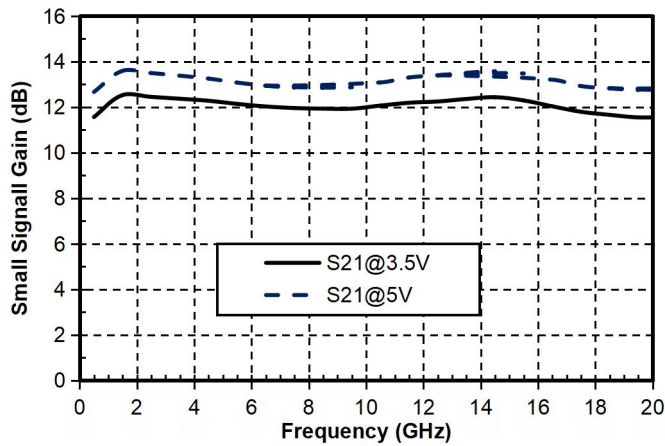
*The noise figure testing instrument is a noise meter.

*+3.5V working static current 15mA.

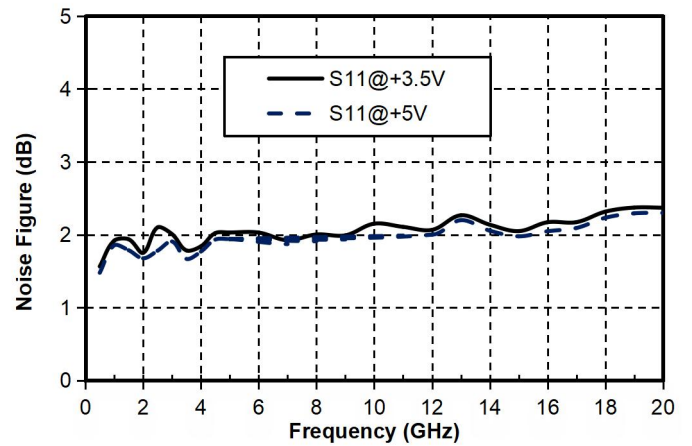
GaAs MMIC Low Noise Amplifier Chip, 0.5-20GHz

Main indicator testing curve

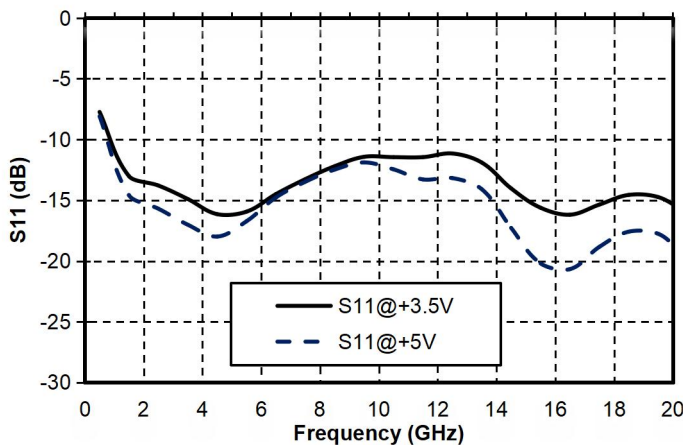
Gain vs. Temperature



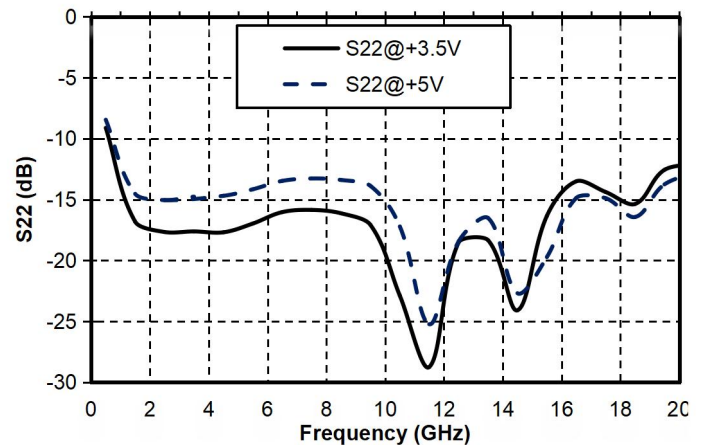
Noise Figure vs. Temperature



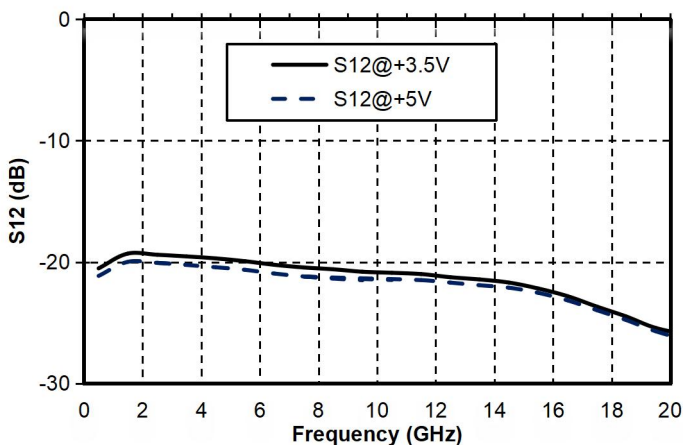
Input return loss vs. Frequency



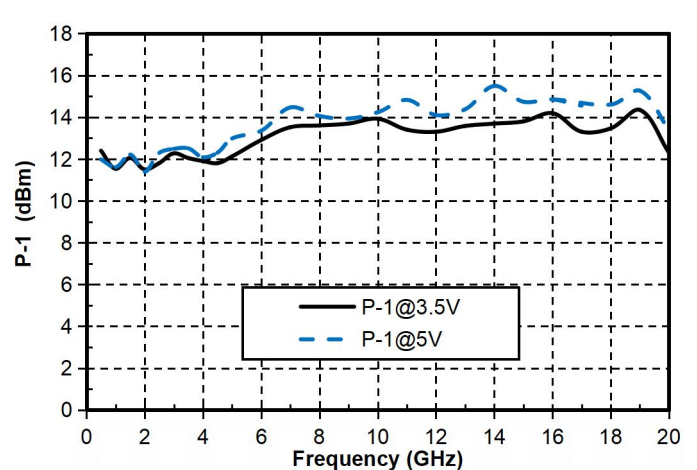
Output return Loss vs. Frequency



Reverse isolation vs. Frequency

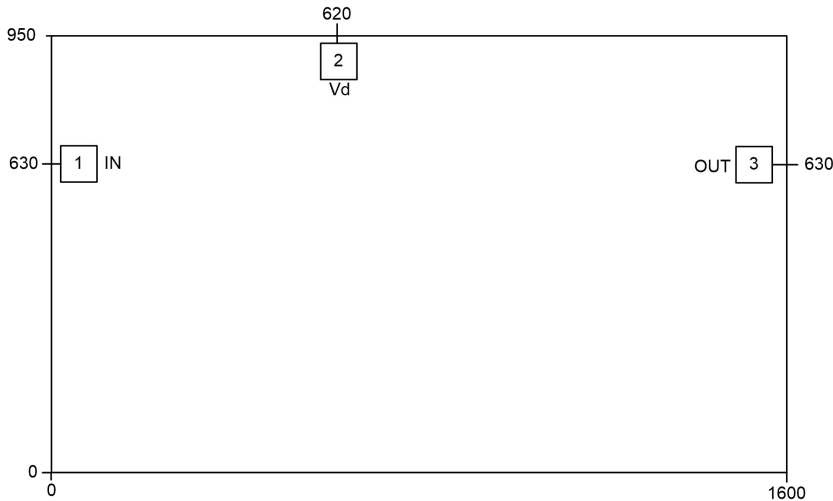


P-1dB vs. Frequency



GaAs MMIC Low Noise Amplifier Chip, 0.5-20GHz

External structure²



【2】 The units in the figure are all millimeters.

Definition of bonding pressure point		
Bond point number	Functional symbols	Function Description
1	RFIN	RF signal input terminal, no need for DC capacitors.
3	RFOUT	RF signal output terminal, no need for DC isolation capacitor.
2	Vd	Amplifier drain bias, requires an external 100pF bypass capacitor.
Chip bottom	GND	The bottom of the chip needs to be well grounded with RF and DC.

Recommended assembly diagram

